

2SB1072(L), 2SB1072(S)

Silicon PNP Triple Diffused

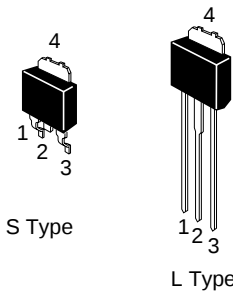
HITACHI

Application

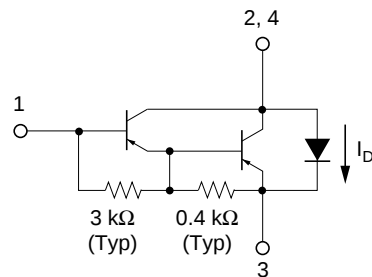
Medium speed power amplifier

Outline

DPAK



- 1. Base
- 2. Collector
- 3. Emitter
- 4. Collector



2SB1072(L), 2SB1072(S)

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-100	V
Collector to emitter voltage	V_{CEO}	-80	V
Emitter to base voltage	V_{EBO}	-7	V
Collector current	I_C	-4	A
C to E diode forward current	I_D^{*1}	4	A
Collector peak current	$I_{C(peak)}$	-8	A
Collector power dissipation	P_C^{*1}	20	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

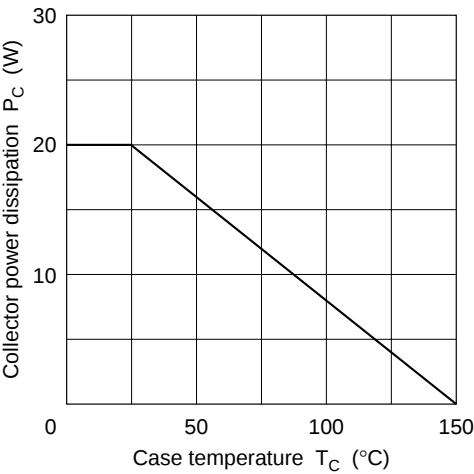
Note: 1. Value at $T_C = 25^\circ\text{C}$

Electrical Characteristics (Ta = 25°C)

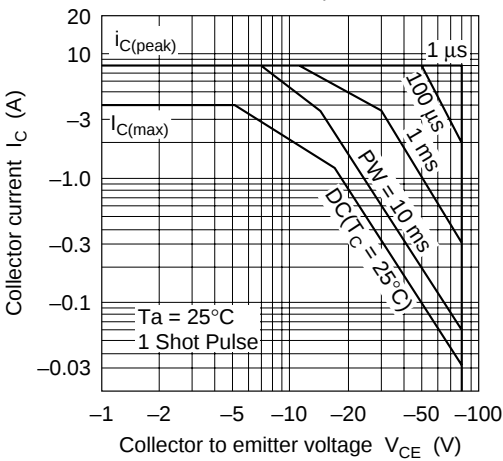
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-80	—	—	V	$I_C = -25\text{ mA}$, $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-7	—	—	V	$I_E = -50\text{ mA}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-100	μA	$V_{CB} = -80\text{ V}$, $I_E = 0$
	I_{CEO}	—	—	-10	μA	$V_{CE} = -60\text{ V}$, $R_{BE} = \infty$
DC current transfer ratio	h_{FE}	1000	—	20000		$V_{CE} = -3\text{ V}$, $I_C = -2\text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{CE(sat)1}$	—	—	-1.5	V	$I_C = -2\text{ A}$, $I_B = -4\text{ mA}^{*1}$
	$V_{CE(sat)2}$	—	—	-3.0	V	$I_C = -4\text{ A}$, $I_B = -40\text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)1}$	—	—	-2.0	V	$I_C = -2\text{ A}$, $I_B = -4\text{ mA}^{*1}$
	$V_{BE(sat)2}$	—	—	-3.5	V	$I_C = -4\text{ A}$, $I_B = -40\text{ mA}^{*1}$
C to E diode forward voltage	V_D	—	—	3.0	V	$I_D = 4\text{ A}^{*1}$
Turn on time	t_{on}	—	0.5	—	μs	$I_C = -2\text{ A}$, $I_{B1} = -I_{B2} = -4\text{ mA}$
Storage time	t_{stg}	—	1.5	—	μs	
Fall time	t_f	—	1.0	—	μs	

Note: 1. Pulse test.

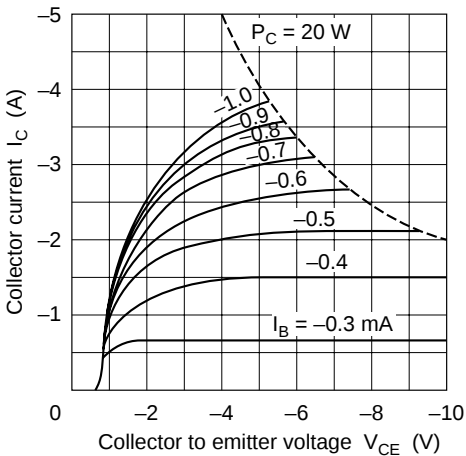
Maximum Collector Dissipation Curve



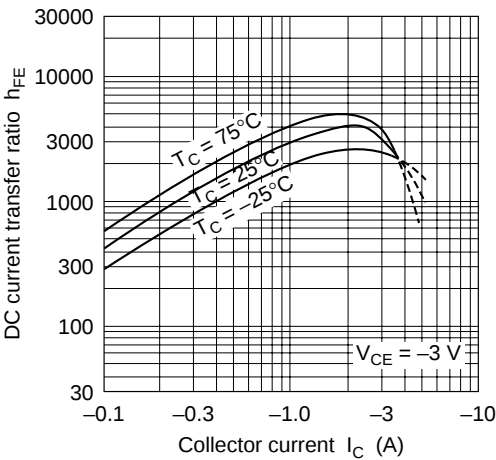
Area of Safe Operation

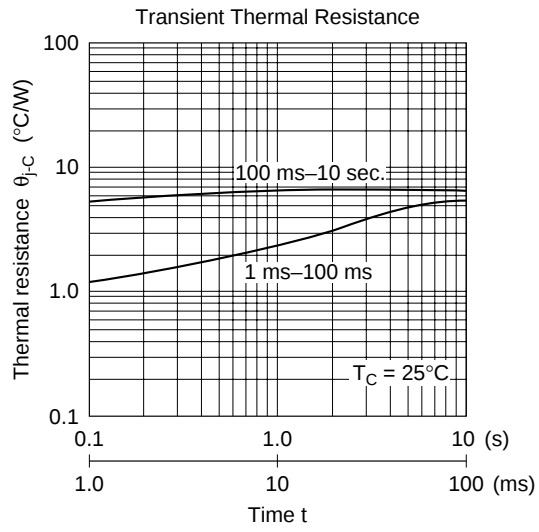
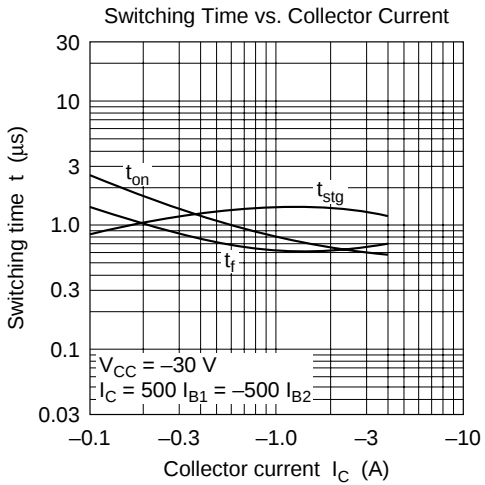
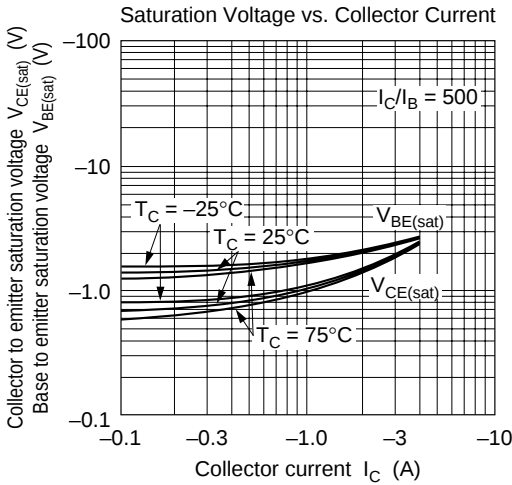


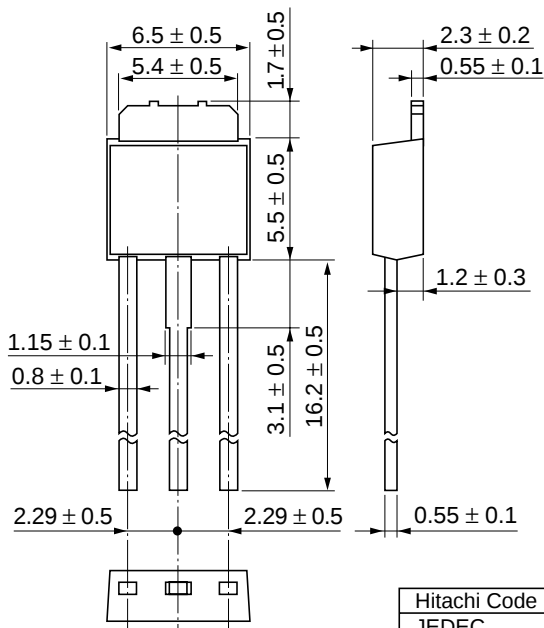
Typical Output Characteristics



DC Current Transfer Ratio vs. Collector Current







Hitachi Code	DPAK (L)-(1)
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.42 g

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